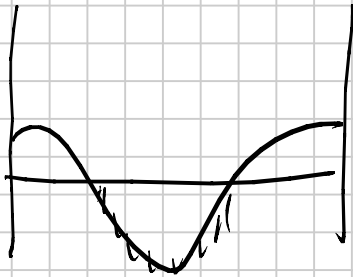


LECTURE #37

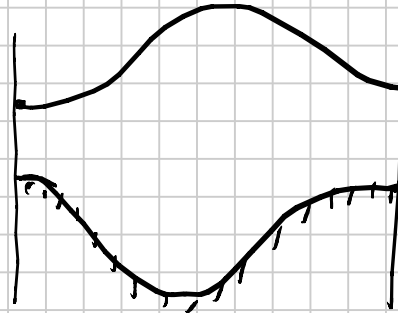
Note Title

4/19/2010

SEMICONDUCTORS



METAL



INSULATOR
FILLED BAND
 \Rightarrow NO CURRENT
 $T = 0$

$T \neq 0 \Rightarrow$ THERMAL EXCITATIONS

$\sigma \neq 0$ AT ROOM TEMPERATURE

$$\rho = \frac{1}{\sigma}$$

$$\rho_{\text{METALS}} \sim 10^{-6} \Omega \text{ cm}$$

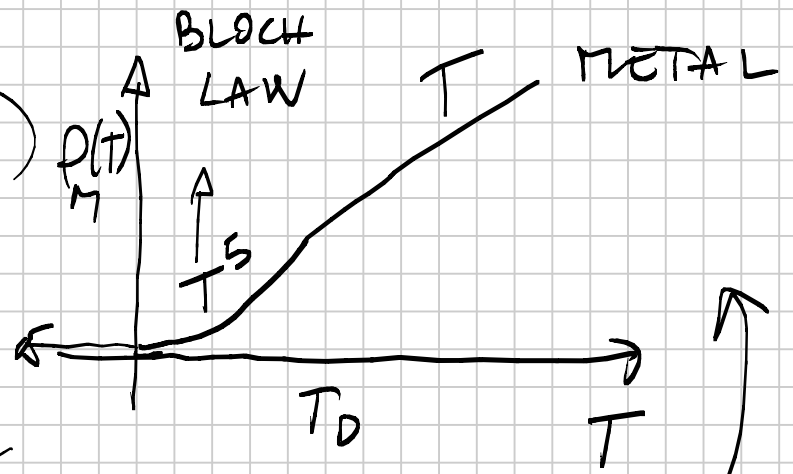
$\rho_{\text{SEMICONDUCTOR}} \sim 10^{-3} \sim 10^9 \text{ } \Omega \text{ cm}$ AT ROOM T

$\rho > 10^9 \sim 10^{22} \text{ } \Omega \text{ cm} \rightarrow$ INSULATORS

$\rho(T)$ DIFFERENT FOR METALS AND SEMICONDUCTORS

METALS

$$\frac{1}{\rho(T)} = \sigma(T) = \frac{m e^2 \tau(T)}{m}$$



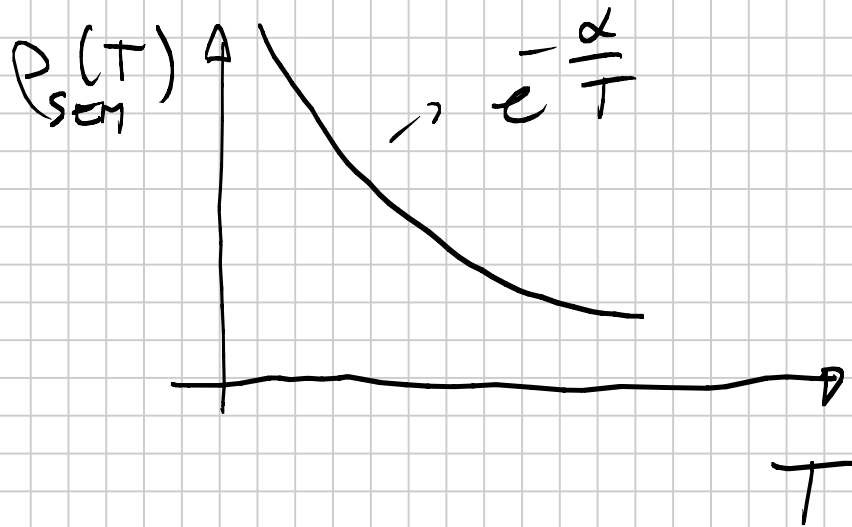
SEMICONDUCTORS

$$\frac{1}{\rho_{\text{SEM}}(T)} = \sigma(T) = \frac{m(T) e^{-\frac{E_g}{2k_B T}}}{m} e^2 \tau(T)$$

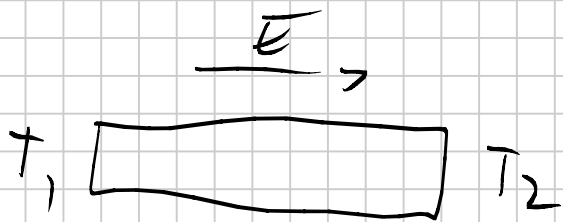
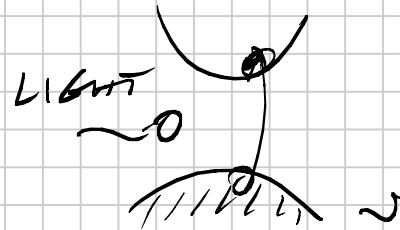
$$\frac{d\rho}{dT} > 0$$

$$\frac{d\rho}{dT} < 0$$

NEGATIVE
DIFFERENTIAL
RESISTIVITY



FINITE E_g
 \Rightarrow PHOTO CONDUCTIVE
 PROPERTIES



→ THERMOPOWER

$$\vec{E} = -(\rho) \nabla T$$

DRUDE \rightarrow $\rho \sim - \frac{C_V}{3ne}$

BOLTZMANN

$$C_V \sim \frac{3}{2} k_B M$$

$Q \sim 100$ BIGGER THAN IN REAL METALS

ELECTRONS ARE WELL DESCRIBED BY BOLTZMANN

Q SEMICONDUCTORS ~ 100 Q METALS

INTRINSIC PROPERTIES

EXTRINSIC " (DOPING WITH IMPURITIES)

GROUP <u>IV</u>		E_{GAP} (eV)	
	C	4	\rightarrow (INSULATOR)
	Si	1.1	
FCC	Ge	0.7	
2 ATOMS / BASIS	Sn	0.2	\rightarrow NARROW GAP SEMICONDUCTOR
(000 / $\frac{a}{4}(1,1,1)$)	Pb	~ 0	METAL

III - V

B

N

Al

P

Ge — As

Im — Sb

Te

FCC

ZINC BLEND

II

VI

Zn

S

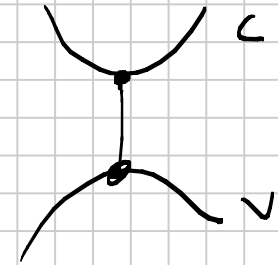
Cd

Se

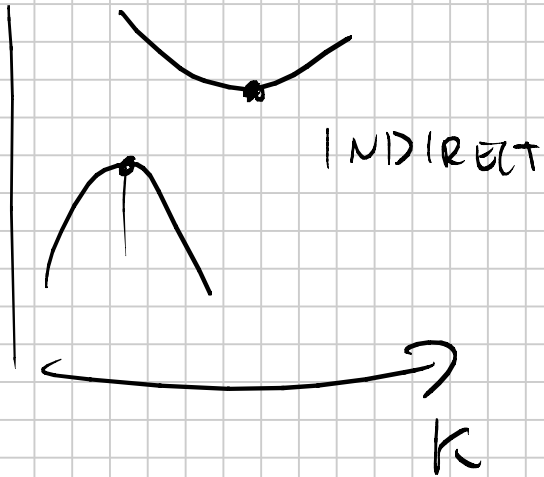
Te

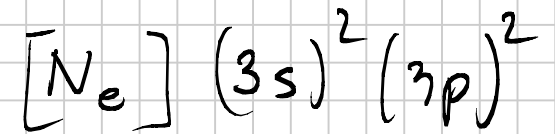
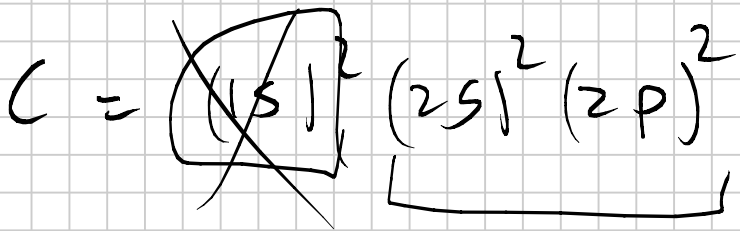
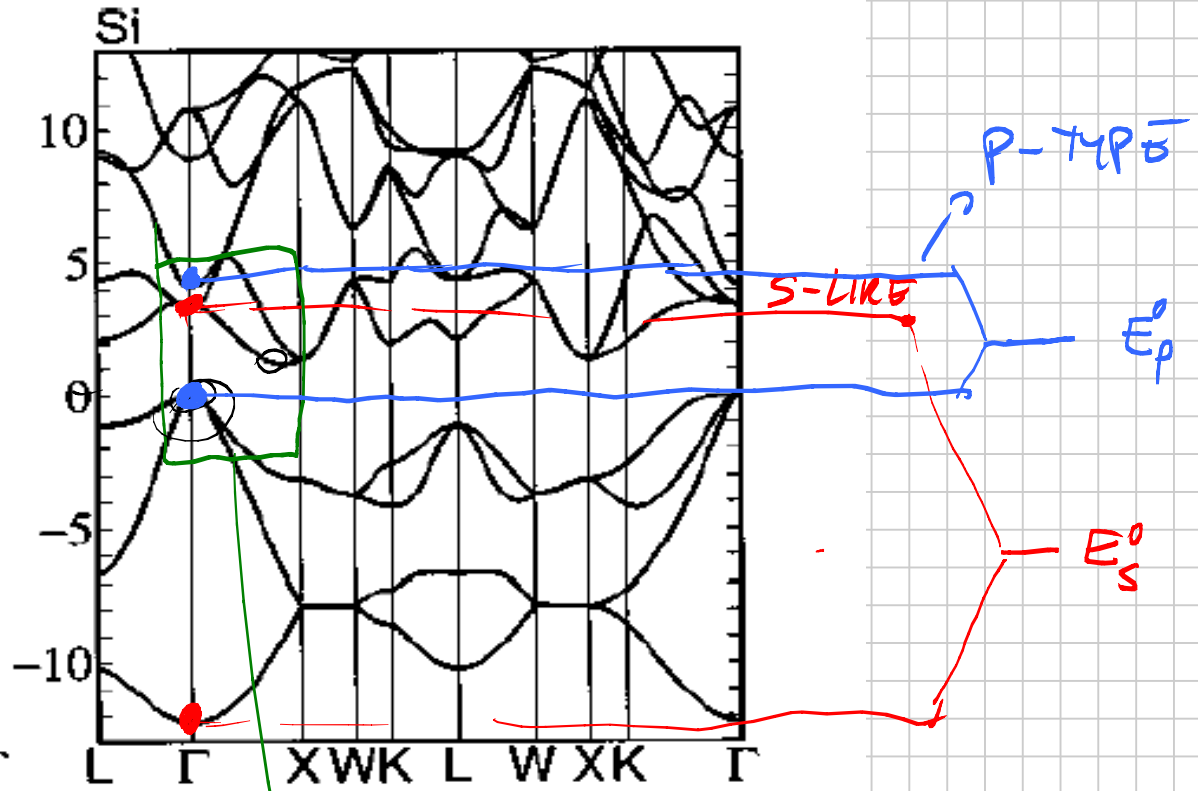
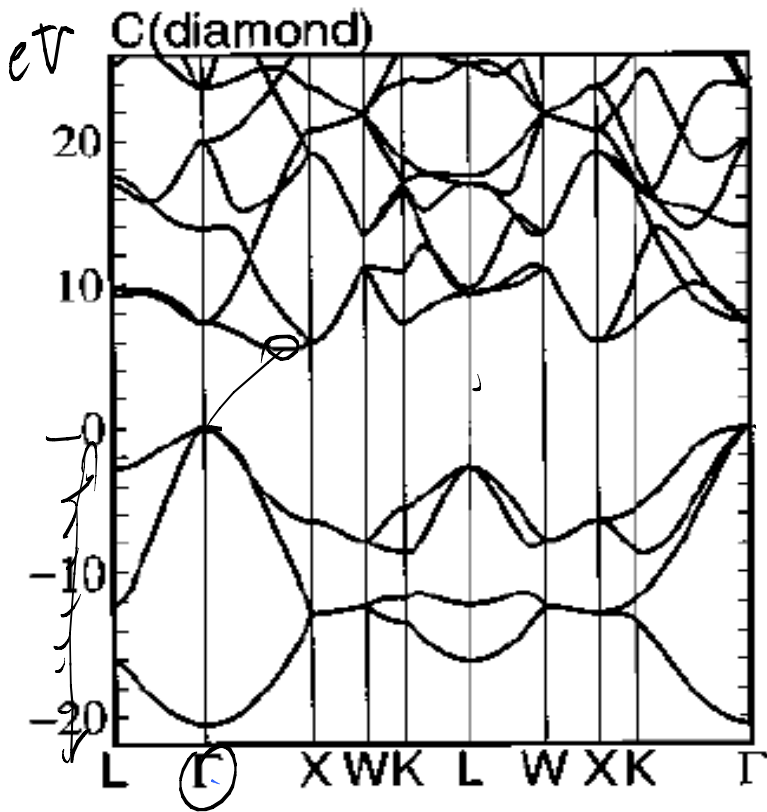


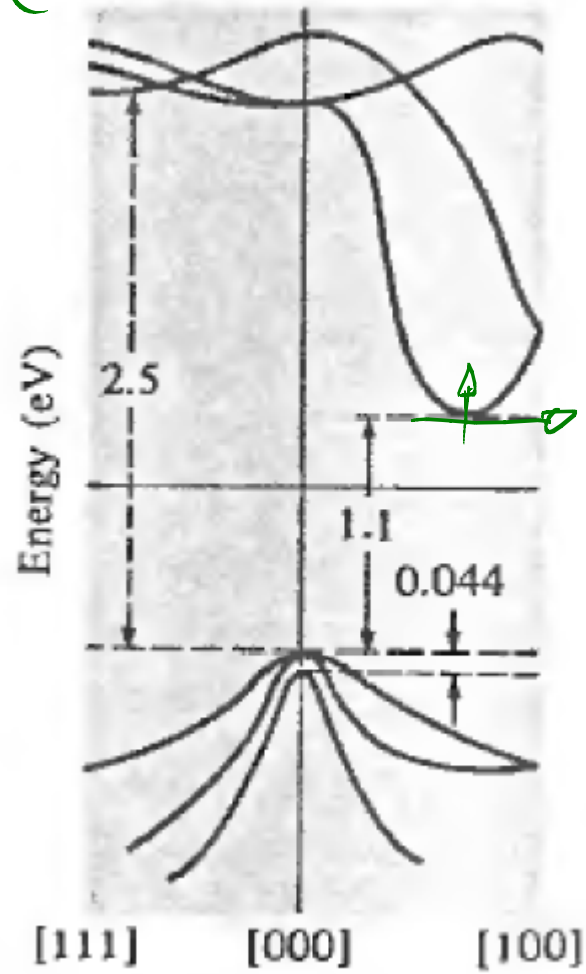
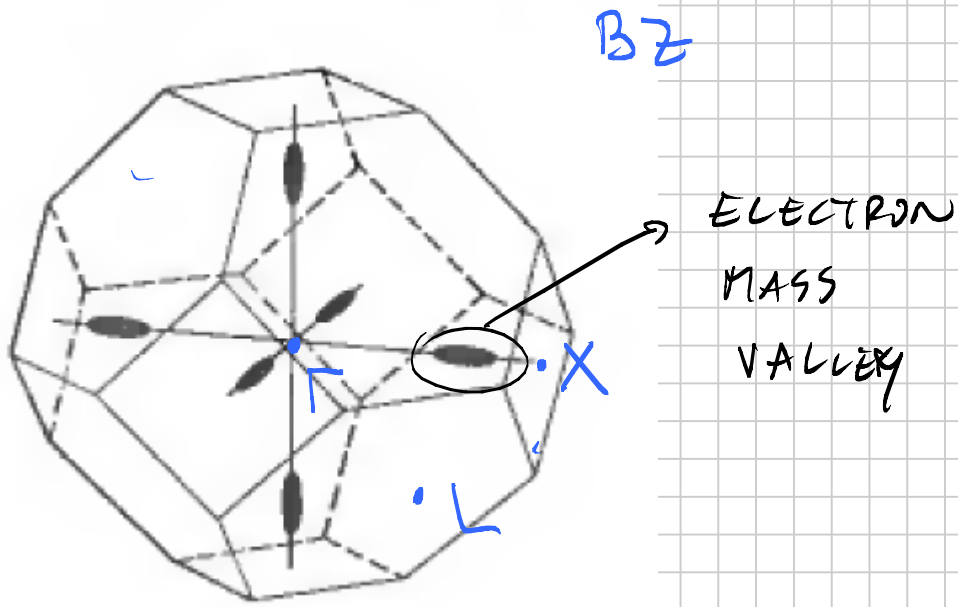
ALSO
HEXAGONAL



DIRECT

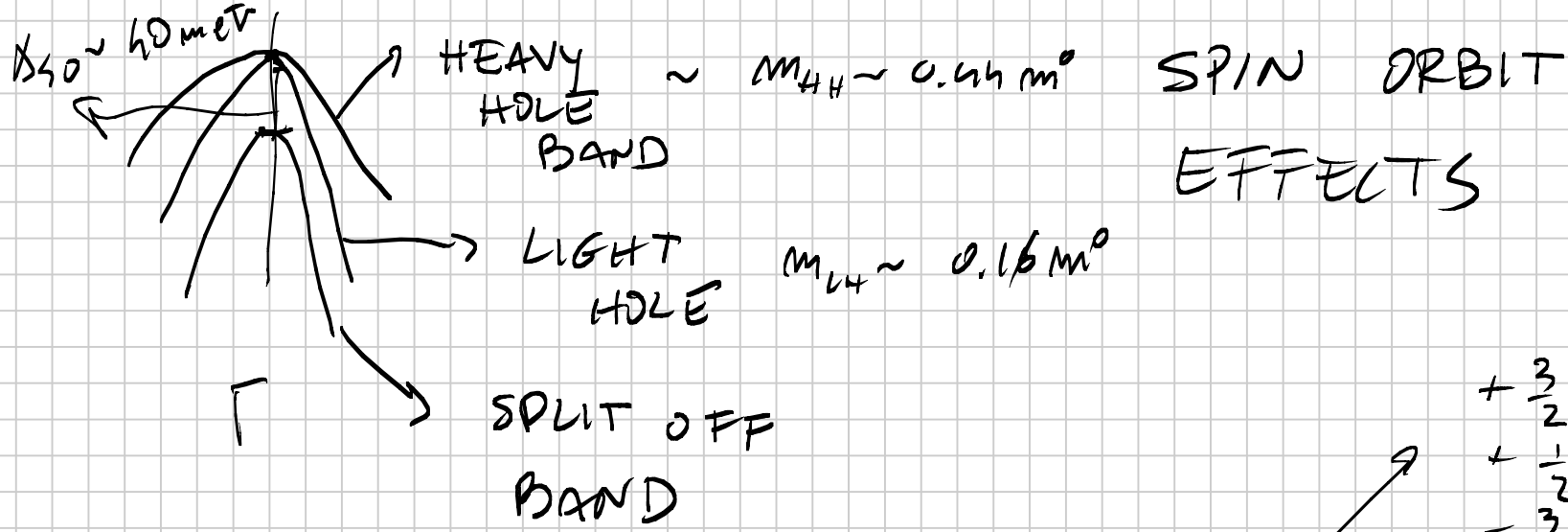






$$m_{eL} = 1.0 m_0$$

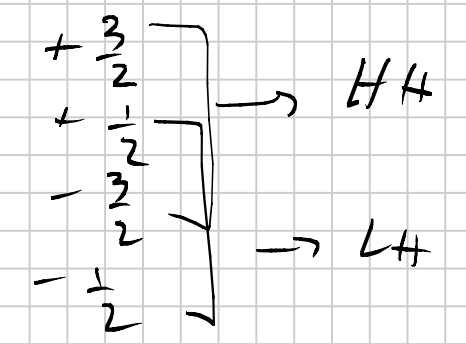
$$m_{eT} \sim 0.2 m_0$$



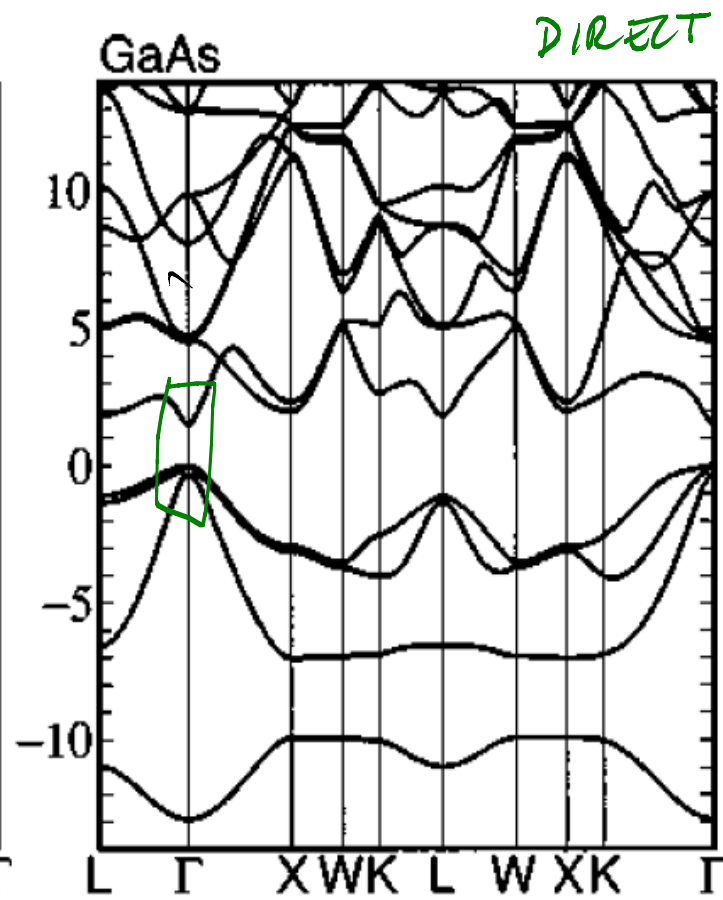
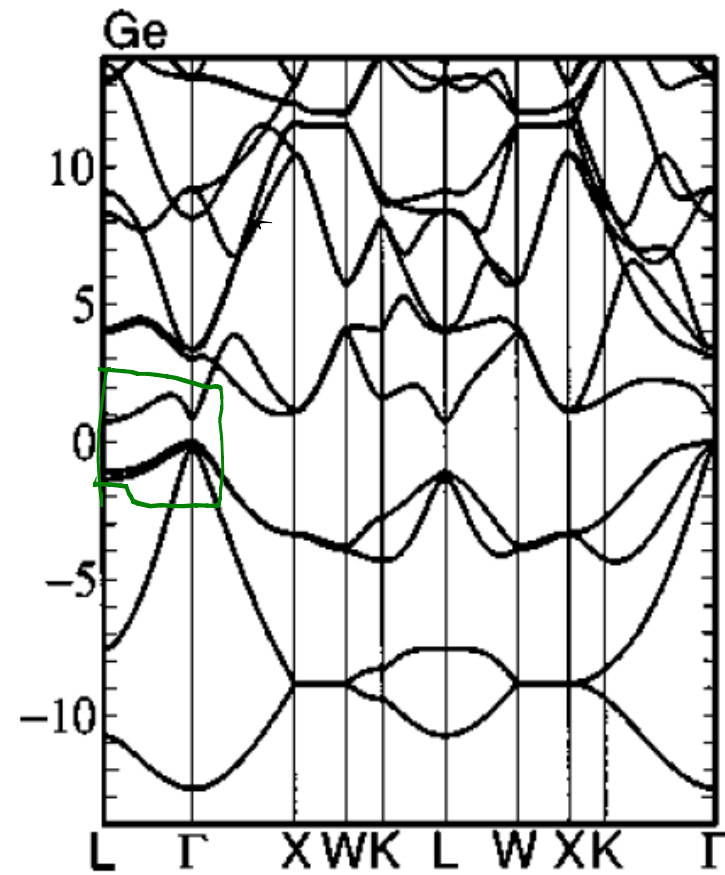
$L = 1$
 $S = \frac{1}{2}$

$\vec{J} = \vec{L} + \vec{S}$

$\vec{J} = \frac{3}{2}$
 $\vec{J} = \frac{1}{2}$

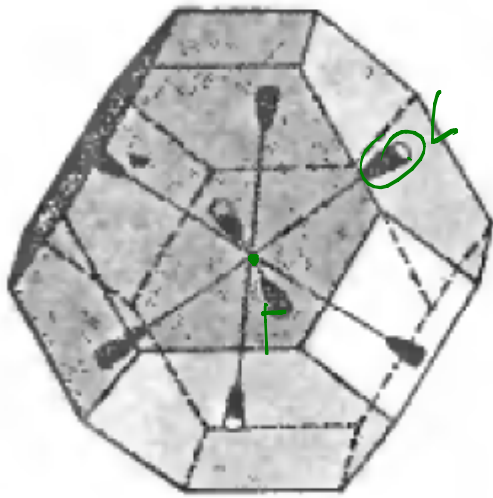


Δ_{SO}



+ STRONG
SPIN
ORBIT

Ge



$\Delta_{50} \sim 300 \text{ meV}$

